

In the Claims:

Please amend claims 1, 4 and 8 in the following manner:

B1
Su. 01

1 --1. (Amended) A process for fabricating a semiconductor device having a
2 buried layer comprising the steps of:
3 implanting an impurity ion [into] region below a surface of a substrate
4 where [the] a buried layer is to be formed in [a] the substrate;
5 [providing] placing the substrate inside a reactor furnace;
6 [preparing] providing a non-oxidizing atmosphere inside of the reactor
7 furnace;
8 annealing the substrate to activate and diffuse the implanted impurity ion
9 region while increasing [inside] the internal temperature of the reactor furnace up to a
10 first temperature; and
11 before the ion implanted region beneath the surface of the substrate
12 expands sufficiently to reach the surface of the substrate, changing [shifting] the [inside]
13 internal temperature of the reactor furnace from the first temperature to a second
14 temperature [in] at which [a] an epitaxial crystal starts to grow on the surface and
15 introducing [a] an epitaxial growth gas into the reactor furnace to [grow] cause an
16 epitaxial layer to grow on [a] the surface of the substrate.--

B2

1 --4. (Amended) The process for fabricating the semiconductor device as set forth
2 in claim 1 further comprising the steps of: